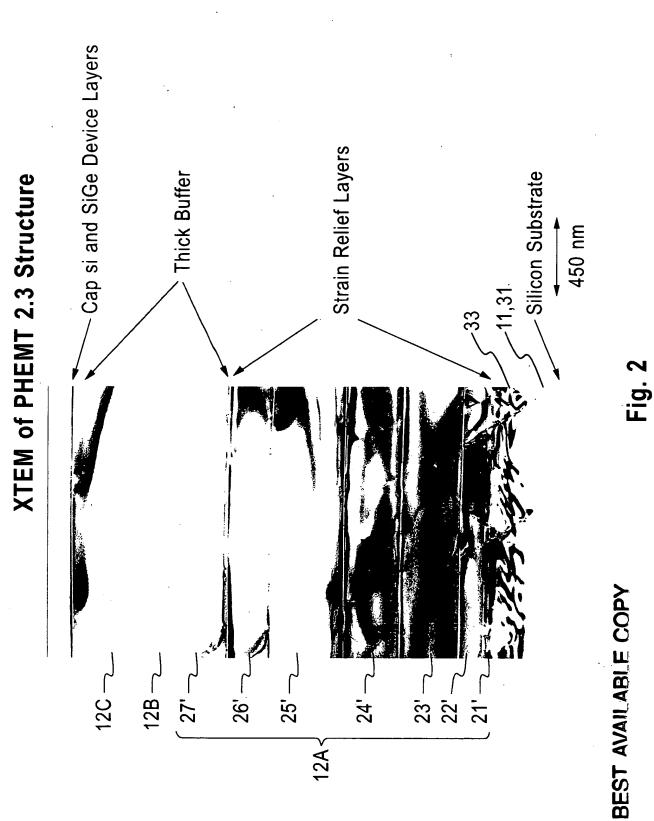


Fig. 1



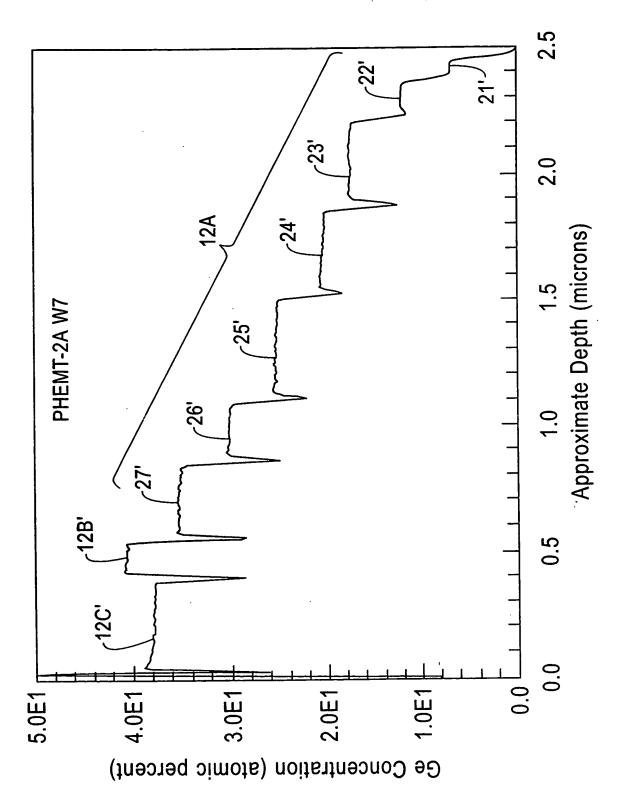
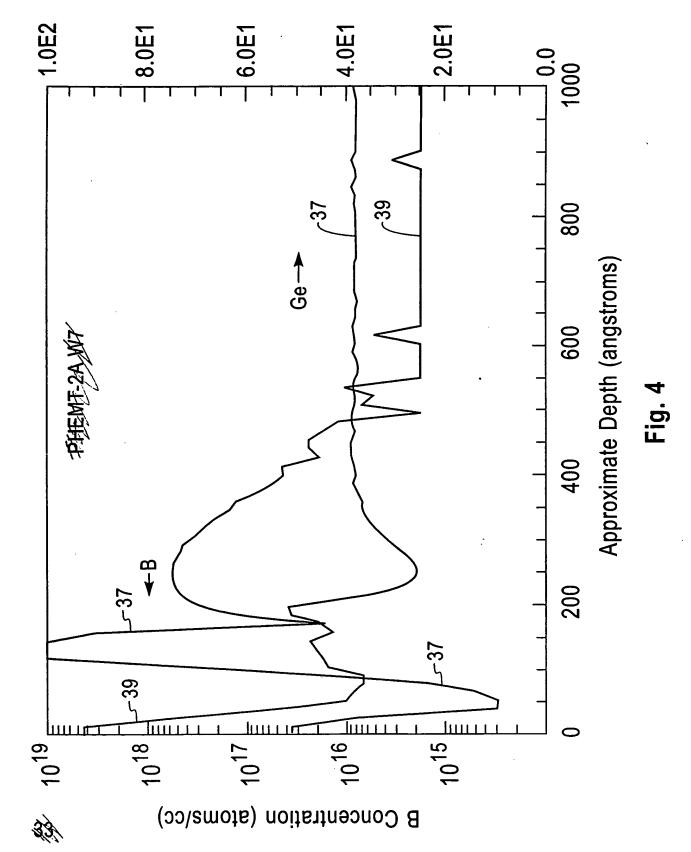
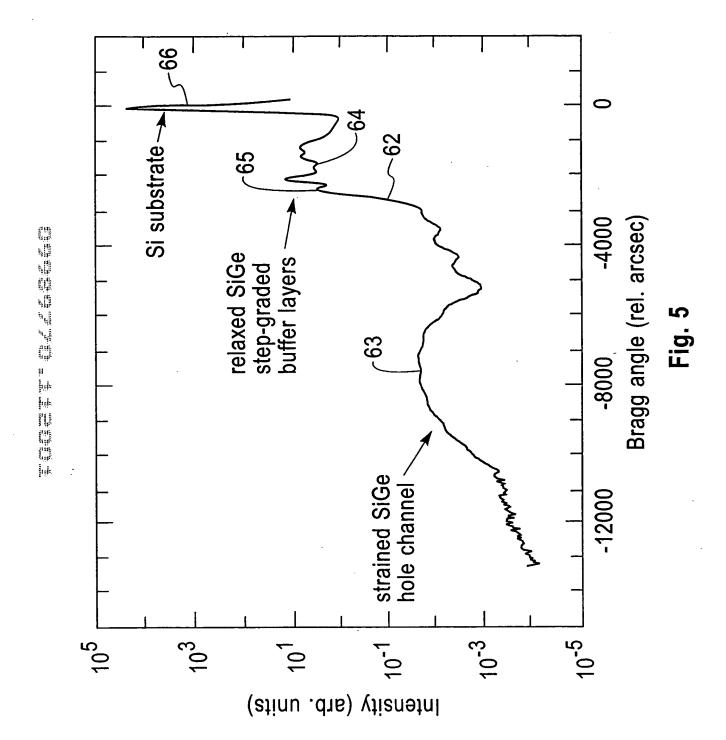


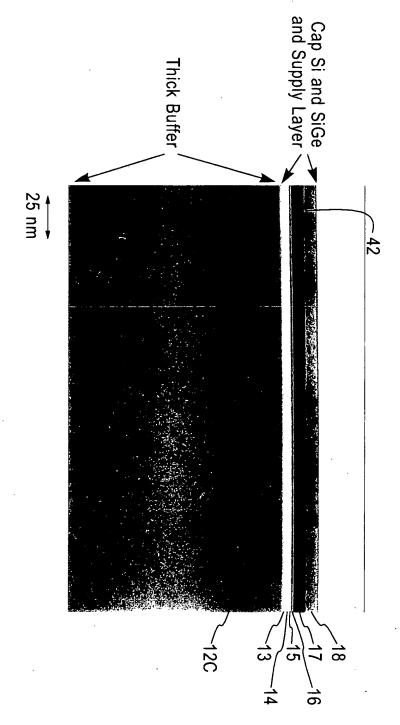
Fig. 3

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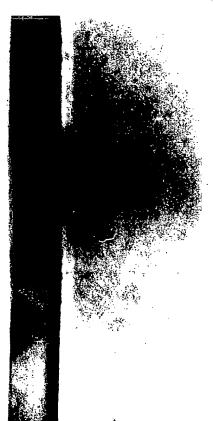


XTEM of PHEMT 2.3 Device



ig. 6

Stacking fault densities $\sim 10^6 - 10^8/\text{cm}^2$



Fia. 7

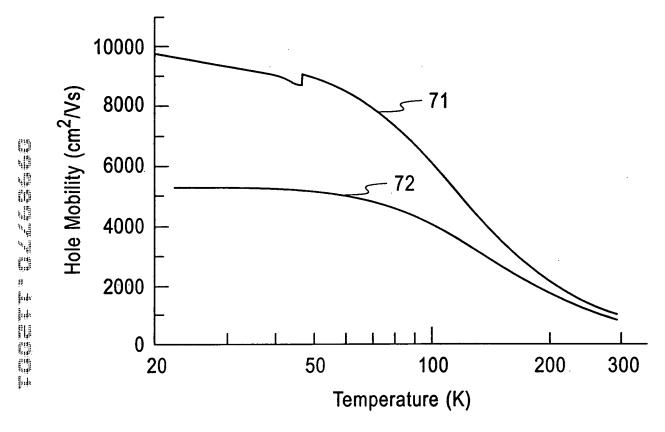


Fig. 8

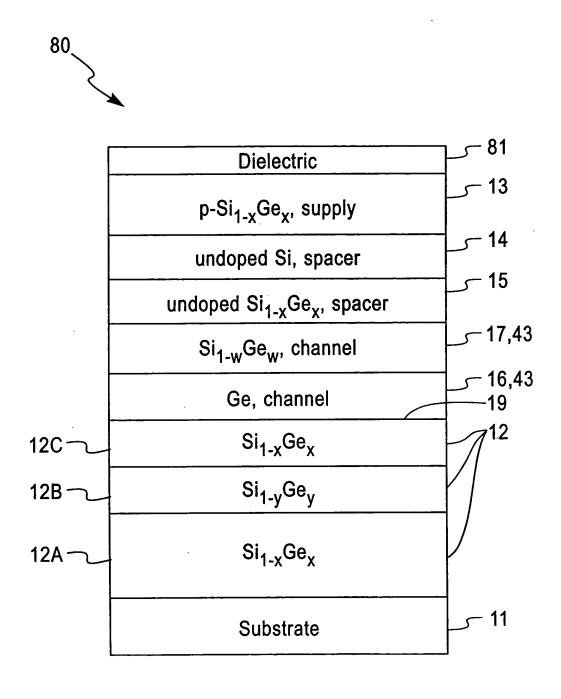
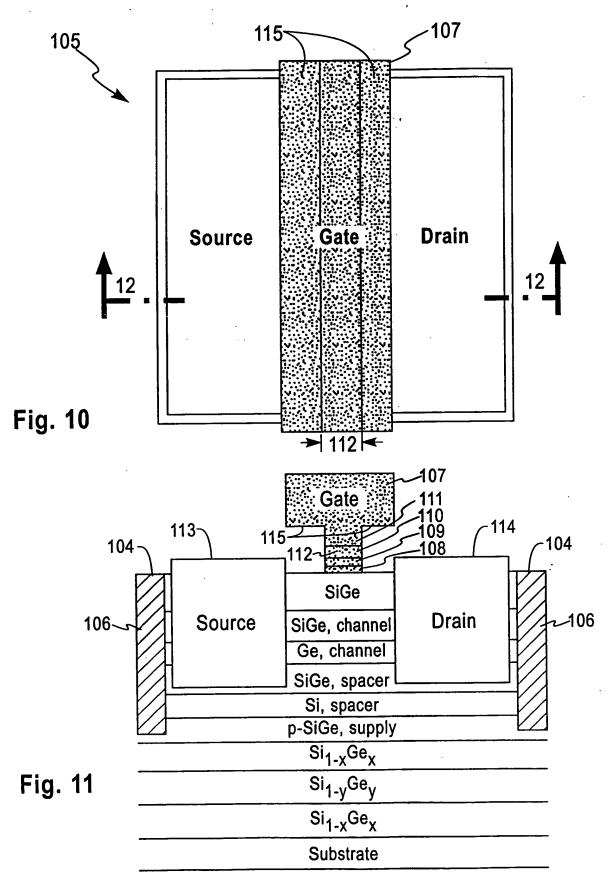


Fig. 9

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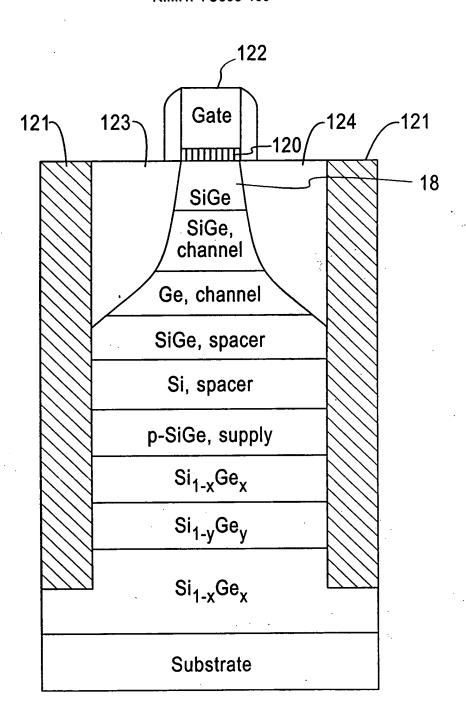


Fig. 12

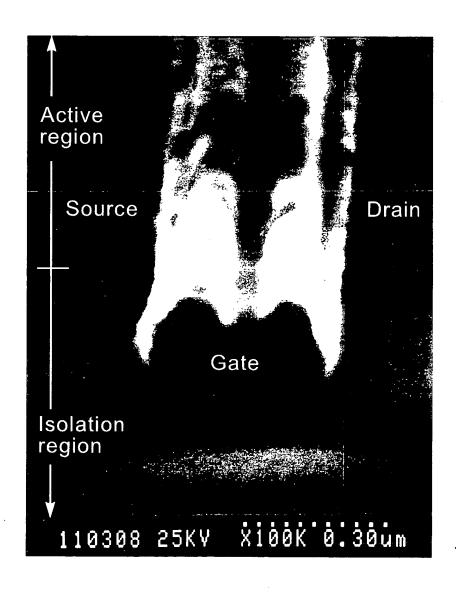


Fig. 13

p-type composite-channel MODFET, L_g = 0.09 μ m, W = 25 μ m

